## Ravi Goel

## List of Publications by Year in descending order

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1684188 1474206 79 10 5 9 citations h-index g-index papers 10 10 10 64 citing authors docs citations times ranked all docs

#	Article	IF	CITATIONS
1	Robust Compact Model of High-Voltage MOSFET's Drift Region. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2023, 42, 337-340.	2.7	8
2	Improved modeling of flicker noise including velocity saturation effect in FinFETs and experimental validation. Microelectronics Journal, 2021, 110, 105020.	2.0	5
3	Compact Modeling of Flicker Noise in High Voltage MOSFETs and Experimental Validation. , 2021, , .		2
4	Analysis and modeling of anomalous flicker noise in long channel halo MOSFETs. Solid-State Electronics, 2021, 181-182, 108028.	1.4	1
5	Modeling of Current Mismatch and $1/\langle i\rangle f\langle i\rangle$ Noise for Halo-Implanted Drain-Extended MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 4794-4801.	3.0	4
6	Accurate and Computationally Efficient Modeling of Nonquasi Static Effects in MOSFETs for Millimeter-Wave Applications. IEEE Transactions on Electron Devices, 2019, 66, 44-51.	3.0	13
7	BSIM-HV: High-Voltage MOSFET Model Including Quasi-Saturation and Self-Heating Effect. IEEE Transactions on Electron Devices, 2019, 66, 4258-4263.	3.0	23
8	Improved Modeling of Bulk Charge Effect for BSIM-BULK Model. IEEE Transactions on Electron Devices, 2019, 66, 2850-2853.	3.0	8
9	Analysis and Modeling of Current Mismatch in Laterally Nonuniform MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 4254-4262.	3.0	3
10	Analysis and Modeling of Temperature and Bias Dependence of Current Mismatch in Halo-Implanted MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 3608-3616.	3.0	12